

产品概览

NTPF082N65S3F: Power MOSFET, N-Channel, SUPERFET® III, FRFET®, 650 V, 40 A, 82 mΩ, TO-220F

欲看完整文档，请参阅数据表。

SUPERFET III MOSFET is ON Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate.

Consequently, SUPERFET III MOSFET is very suitable for the various power systems for miniaturization and higher efficiency. SUPERFET III FRFET MOSFET's optimized reverse recovery performance of body diode can remove additional component and improve system reliability.

特性

- 700 V @ T_J = 150 °C
- Ultra Low Gate Charge (Typ. Q_g = 70 nC)
- Low Effective Output Capacitance (Typ. C_{oss}(eff.) = 680 pF)
- Optimized Capacitance
- Excellent body diode performance (low Q_{rr}, robust body diode)
- Typ. R_{DS(on)} = 70 mΩ
- 100% Avalanche Tested
- RoHS Compliant

应用

- Telecommunication
- Cloud system
- Industrial

优势

- Higher system reliability at low temperature operation
- Lower switching loss
- Lower switching loss
- Lower peak V_{ds} and lower V_{gs} oscillation
- Higher system reliability in LLC and Phase shift full bridge circuit

终端产品

- Telecom power
- Server power
- Solar / UPS
- EV charger

器件电气规格

产品	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	V _{(BR)DSS} Min (V)	V _{GS} Max (V)	V _{GS(th)} Max (V)	I _D Max (A)	P _D Max (W)	R _{DS(on)} Max @ V _{GS} = 2.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 4.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 10 V (mΩ)	Q _g Typ @ V _{GS} = 4.5 V (nC)	Q _g Typ @ V _{GS} = 10 V (nC)	C _{iss} Typ (pF)	Package Type
NTPF082N65S3F	2.2222	Pb-free Halide free	Active	N-Channel	Single	650	30	5	40	48	-	-	82	-	70	3240	TO-220-3 FullPak

欲了解更多信息，请联系您当地的销售支援 www.onsemi.cn。

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